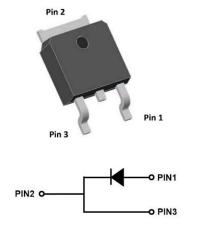


YJD106504DYG4

Silicon Carbide Schottky Diode

V _{RRM}	650V
I _{F(135°C)}	6A
Q _C	11nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
 Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- Package: TO-252
- Terminals: Tin plated leads
- Polarity: As marked

■Maximum Ratings (T_c=25[°]C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Device marking code			D106504DYG4
Reverse voltage (Repetitive peak) @ T _j =25°C	V _{RRM}	V	650
Reverse voltage (Surge peak) @ T _j =25°C	V _{RSM}	V	650
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	650
Continuous forward current @ $T_c=25^{\circ}C$		А	12.6
Continuous forward current @ T _C =135°C	I _F		6
Continuous forward current @ T _c =154°C			4
Non-repetitive peak forward surge current @ $T_c=25^{\circ}C$, tp=10ms, Half Sine Wave	I _{FSM}	А	28
Power Dissipation@ $T_c=25^{\circ}C$	Ρ _{τοτ}	W	57
Power Dissipation@ T _c =110°C	Гтот		25
i²t Value@ Tc=25°C ,tp=10ms	∫ i²dt	A ² S	3.9
Operating junction and Storage temperature range	T _j ,T _{stg}	°C	-55 to +175

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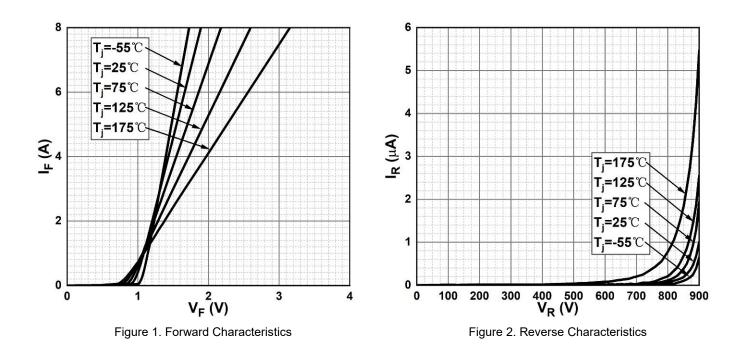
Electrical Characteristics

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.			
	V _F	V	I _F =4A, T _j =25°C	1.45	1.65			
Forward voltage drop	VF		I _F =4A, Tj=175°C	2.0	-			
Deveree europt	I _R			V _R =650V, T _j =25°C	0.1	20		
Reverse current		μA	V _R =650V, T _j =175°C	1	-			
Total capacitive charge	Qc	nC	V_R =400V, T _j =25°C , Q_C = \int_0^{VR} C(V)dV	11	-			
	C pF					V _R =0V, f=1MHZ	194	-
Total capacitance		C pF	V _R =200V, f=1MHZ	20.5	-			
		V _R =400V, f=1MHZ	19.5	-				
Capacitance stored energy	Ec	μJ	V _R =400V	1.34	-			

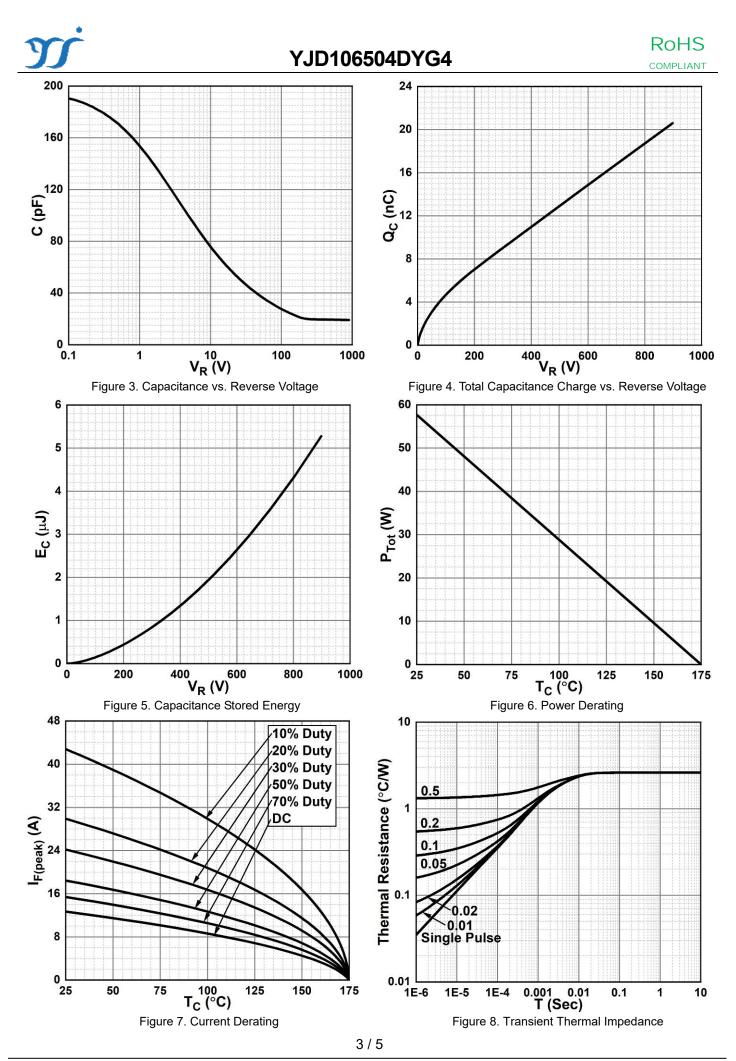
■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{_{ ext{ hetaJ-C}}}$	°C <i>W</i>	2.60

■Typical Characteristics



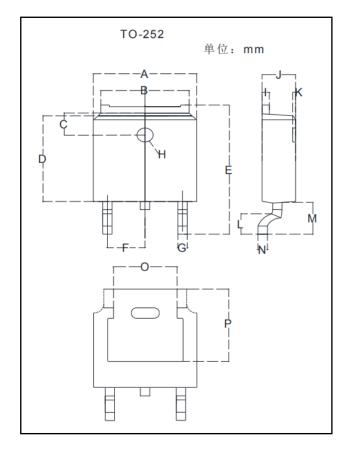
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Yangzhou Yangjie Electronic Technology Co., Ltd.



Outline Dimensions



TO-252		
Dim	Min	Max
А	6.50	6.70
В	5.10	5.46
С	1.40	1.80
D	6.00	6.20
E	10.00	10.40
F	2.17	2.37
G	0.66	0.86
Н	Φ1.05	Ф1.35
I	0.46	0.58
J	2.20	2.40
К	0.00	0.30
L	0.89	2.29
М	2.73	3.08
Ν	0.43	0.58
0	4.20	4.95
Р	5.15	5.45



Disclaimer

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

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